

DOCKET NO: 244278US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
HIDETAKA HATTORI, ET AL. : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW U.S. PCT APPLN. :  
(Based on 10/294,583)  
FILED: HERewith :  
• FOR: POWER SEMICONDUCTOR :  
ELEMENT CAPABLE OF  
IMPROVING SHORT CIRCUIT  
WITHSTAND CAPABILITY WHILE  
MAINTAINING LOW ON-  
VOLTAGE AND METHOD OF  
FABRICATING THE SAME

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Abstract** begin on page 8 of this paper and include an attached replacement sheet.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 9 of this paper.

**Remarks/Arguments** begin on page 11 of this paper.